



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Confirmation No. 7689

YAMAGATA et al.

Allowed: January 2, 2004

Serial No. 09/993,890

Atty Ref.: 925-219

Filed: November 27, 2001

Group: 2825

For: METHOD FOR MANUFACTURING
NONVOLATILE SEMICONDUCTOR MEMORY
WITH NARROW VARIATION IN THRESHOLD
VOLTAGES OF MEMORY CELLS

Examiner: Lee, Calvin

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March 29, 2004

Mail Stop: Issue Fee

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

Sir:

The instant application was allowed January 2, 2004. However, the Reasons for Allowance are not commensurate with the scope of the claims.

For example, and without limitation, claims 1 and 5 do not require "thermally oxidizing the sidewall of a floating gate."

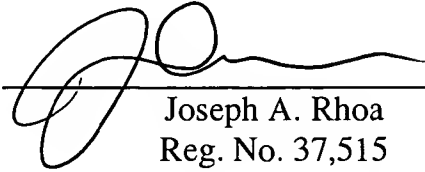
Please let me know if you should have any questions.

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Respectfully submitted,

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By:



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